

# 2SA2140

## Silicon PNP epitaxial planar type

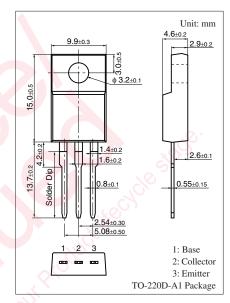
For power amplification
For TV VM circuit

#### ■ Features

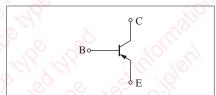
- Satisfactory linearity of forward current transfer ratio h<sub>FE</sub>
- High transition frequency (f<sub>T</sub>)
- Full-pack package which can be installed to the heat sink with one screw.

## ■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

Symbol	Rating	Unit	
$V_{CBO}$	-180	V	
$V_{CEO}$	-180	V	
$V_{EBO}$	-6	V	
$I_{C}$	-1.5	A	
$I_{CP}$	-3	A	
P <sub>C</sub>	20	W	
	2.0	(10)	
$T_{j}$	150	°C	
T <sub>stg</sub>	-55 to +150	o °C×(	
	$\begin{array}{c} V_{CBO} \\ V_{CEO} \\ \end{array}$ $\begin{array}{c} V_{CEO} \\ \end{array}$ $\begin{array}{c} I_{C} \\ \end{array}$ $\begin{array}{c} I_{CP} \\ \end{array}$ $\begin{array}{c} P_{C} \\ \end{array}$	$\begin{array}{c cccc} V_{CBO} & -180 \\ V_{CEO} & -180 \\ \hline V_{CEO} & -180 \\ \hline V_{EBO} & -6 \\ \hline I_{C} & -1.5 \\ \hline I_{CP} & -3 \\ \hline P_{C} & 20 \\ \hline \hline 2.0 \\ \hline T_{j} & 150 \\ \hline \end{array}$	



#### Internal Connection



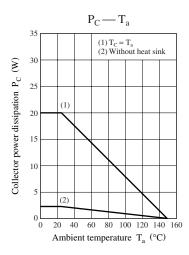
## ■ Electrical Characteristics T<sub>C</sub> = 25°C ± 3°C

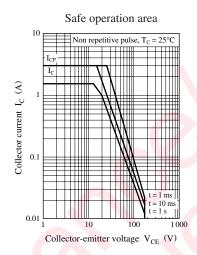
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-180			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -180 \text{ V}, I_E = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-100	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = -5 \text{ V}, I_{C} = -0.1 \text{ A}$	60		240	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -1 A, I_B = -0.1 A$			- 0.5	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_{C} = -0.2 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		30		pF
(Common base, input open circuited)		So Ville				
Turn-on time	t <sub>on</sub>	$I_C = -0.4$ A, Resistance loaded		0.1		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.04 \text{ A}, I_{B2} = -0.04 \text{ A}$		1.0		μs
Fall time	t <sub>f</sub>	$V_{CC} = 100 \text{ V}$		0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р
$h_{FE}$	60 to 140	120 to 240





2

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